

5082-2800

High breakdown general purpose Schottky diode

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Description

Lifecycle status: **Active**

Features

The 5082-28xx family are passivated Schottky barrier diodes which use a patented guard-ring design to achieve a high breakdown voltage. Packaged in a low cost glass package, they are well suited to high level detecting, mixing, switching, gating, log or A-D converting, video detecting, frequency discriminating, sampling, and wave shaping applications.

1N5711, 1N5712, 5082-2800 Series

Schottky Barrier Diodes for General Purpose Applications



Data Sheet

Description/Applications

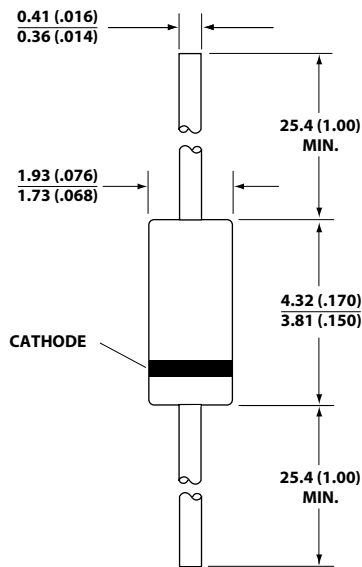
The 1N5711, 1N5712, 5082-2800/10/11 are passivated Schottky barrier diodes which use a patented "guard ring" design to achieve a high breakdown voltage. Packaged in a low cost glass package, they are well suited for high level detecting, mixing, switching, gating, log or A-D converting, video detecting, frequency discriminating, sampling, and wave shaping.

The 5082-2835 is a passivated Schottky diode in a low cost glass package. It is optimized for low turn-on voltage. The 5082-2835 is particularly well suited for the UHF mixing needs of the CATV marketplace.

Features

- Low Turn-On Voltage As Low as 0.34 V at 1 mA
- Pico Second Switching Speed
- High Breakdown Voltage Up to 70 V
- Matched Characteristics Available

Outline 15



DIMENSIONS IN MILLIMETERS AND (INCHES).

Maximum Ratings

Junction Operating and Storage Temperature Range

1N5711, 1N5712, 5082-2800/10/11 -65°C to +200°C

5082-2835 -60°C to +150°C

DC Power Dissipation

(Measured in an infinite heat sink at $T_{CASE} = 25^{\circ}C$)

Derate linearly to zero at maximum rated temp.

1N5711, 1N5712, 5082-2800/10/11 250 mW

5082-2835 150 mW

Peak Inverse Voltage V_{BR}

Package Characteristics

Outline 15

| | |
|----------------------------------|-----------------|
| Lead Material | Dumet |
| Lead Finish | 95-5% Tin-Lead |
| Max. Soldering Temperature | 260°C for 5 sec |
| Min. Lead Strength | 4 pounds pull |
| Typical Package Inductance | |
| 1N5711, 1N5712:..... | 2.0 nH |
| 2800 Series:..... | 2.0 nH |
| Typical Package Capacitance | |
| 1N5711, 1N5712:..... | 0.2 pF |
| 2800 Series:..... | 0.2 pF |

The leads on the Outline 15 package should be restricted so that the bend starts at least 1/16 inch from the glass body.

Outline 15 diodes are available on tape and reel. The tape and reel specification is patterned after RS-296-D.

Electrical Specifications at $T_A = 25^\circ\text{C}$

General Purpose Diodes

| Part Number | Package Outline | Min. Breakdown Voltage | Max. Forward Voltage | $V_F = 1\text{ V Max. at Forward Current}$ | Max. Reverse Leakage Current | | Max. Capacitance |
|-----------------|-----------------|--|----------------------|--|--------------------------------|----|--|
| | | $V_{BR} (V)$ | $V_F (mV)$ | $I_F (mA)$ | $I_R (nA) \text{ at } V_R (V)$ | | $C_T (pF)$ |
| 5082-2800 | 15 | 70 | 410 | 15 | 200 | 50 | 2.0 |
| 1N5711 | 15 | 70 | 410 | 15 | 200 | 50 | 2.0 |
| 5082-2810 | 15 | 20 | 410 | 35 | 100 | 15 | 1.2 |
| 1N5712 | 15 | 20 | 550 | 35 | 150 | 16 | 1.2 |
| 5082-2811 | 15 | 15 | 410 | 20 | 100 | 8 | 1.2 |
| 5082-2835 | 15 | 8* | 340 | 10* | 100 | 1 | 1.0 |
| Test Conditions | | $I_R = 10 \mu A$ $*I_R = 100 \mu A$ | $I_F = 1\text{ mA}$ | $*V_F = 0.45\text{ V}$ | | | $V_R = 0\text{ V}$ $f = 1.0\text{ MHz}$ |

Note: Effective Carrier Lifetime (τ) for all these diodes is 100 ps maximum measured with Krakauer method at 5 mA except for 5082-2835 which is measured at 20 mA.

Matched Pairs and Quads

| Basic Part Number 5082- | Matched Pair Unconnected | Matched Quad Unconnected | Batch Matched ^[1] | Test Conditions |
|----------------------------|---|---|--|---|
| 2800 | 5082-2804 $\Delta V_F = 20 \text{ mV}$ | 5082-2805 $\Delta V_F = 20 \text{ mV}$ | | ΔV_F at $I_F = 0.5, 5 \text{ mA}$ * $I_F = 10 \text{ mA}$ ΔC_O at $f = 1.0 \text{ MHz}$ |
| 2811 | | | 5082-2826 $\Delta V_F = 10 \text{ mV}$ $\Delta C_O = 0.1 \text{ pF}$ | ΔV_F at $I_F = 10 \text{ mA}$ ΔC_O at $f = 1.0 \text{ MHz}$ |
| 2835 | | | 5082-2080 $\Delta V_F = 10 \text{ mV}$ $\Delta C_O = 0.1 \text{ pF}$ | ΔV_F at $I_F = 10 \text{ mA}$ ΔC_O at $f = 1.0 \text{ MHz}$ |

Note:

1. Batch matched devices have a minimum batch size of 50 devices.

SPICE Parameters

| Parameter | Units | 5082-2800 | 5082-2810 | 5082-2811 | 5082-2835 |
|-----------|----------|-----------------------|-----------------------|-----------------------|-----------------------|
| B_V | V | 75 | 25 | 18 | 9 |
| C_{J0} | pF | 1.6 | 0.8 | 1.0 | 0.7 |
| E_G | eV | 0.69 | 0.69 | 0.69 | 0.69 |
| I_{BV} | A | $10E-5$ | $10E-5$ | $10E-5$ | $10E-5$ |
| I_S | A | $2.2 \times 10E^{-9}$ | $1.1 \times 10E^{-9}$ | $0.3 \times 10E^{-8}$ | $2.2 \times 10E^{-8}$ |
| N | | 1.08 | 1.08 | 1.08 | 1.08 |
| R_S | Ω | 25 | 10 | 10 | 5 |
| P_B | V | 0.6 | 0.6 | 0.6 | 0.56 |
| P_T | | 2 | 2 | 2 | 2 |
| M | | 0.5 | 0.5 | 0.5 | 0.5 |

Diode Package Marking

1N5xxx 5082-xxxx

would be marked:

1Nx xx

xxx xx

YWW YWW

where xxxx are the last four digits of the 1Nxxxx or the 5082-xxxx part number.

Y is the last digit of the calendar year. WW is the work week of manufacture.

Examples of diodes manufactured during workweek 45 of 1999:

1N5712 5082-3080

would be marked:

1N5 30

712 80

945 945

Part Number Ordering Information

| Part Number | No. of devices | Container |
|---------------------------|----------------|----------------|
| 5082-28xx#T25/1N57xx#T25 | 2500 | Tape & Reel |
| 5082-28xx#T50/ 1N57xx#T50 | 5000 | Tape & Reel |
| 5082-28xx/ 1N57xx | 100 | Antistatic bag |